## **Supplementary Material**

the results of motioning the impedance of the sample decorang to the scheme in Fig. 5.											
<i>Т</i> , °С	$r_1$ , W	$r_2, W$	$T_{\rm cpe1}$	P <sub>cpe1</sub>	<i>r</i> <sub>3</sub> , W	T <sub>cpe2</sub>	P <sub>cpe2</sub>	$r_4$ , W	T <sub>cpe3</sub>	$P_{\rm cpe3}$	$\chi^2 \cdot 10^4$
22	-998	2.065e6		0.959	1.139e7	3.653e-9	0.868	-	-	-	17
100	460	54438		1	1.852e5	4.393e-9	0.913	6.81e6	1.008e-7	0.767	9
125	622	26753	2.66e-11	1	73397	3.78e-9	0.941	1.832e6	1.218e-7	0.777	9
150	549	13108	1.444e-11	1	32395	4.166e-9	0.935	6.577e5	1.485e-7	0.777	3.5
175	546	6703	1.555e-11	1	15436	5.19e-9	0.916	2.553e5	1.712e-7	0.788	2.2
200	-	3993	1.684e-11	1	7685	7.305e-9	0.887	1.104e5	1.92e-7	0.795	2.4
225	-	2332	1.935e-11	1	3866	5.921e-9	0.904	51133	2.265e-7	0.790	2.9
250	-	1429	1.74e-11	1	2068	4.194e-9	0.945	23511	2.34e-7	0.800	3.9
275	-	954	1.85e-11	1	1224	5.241e-9	0.928	10641	2.266e-7	0.816	3.8
300	-	643	1.91e-11	1	733	8.228-9	0.895	4592	2.019e-7	0.837	3.7
325	-	411	2.04e-11	1	497.5	9.335e-9	0.878	1968	1.577e-7	0.867	4.7
350	-	295	2.34e-11	-	330.3	1.185e-8	0.858	877	1.269e-7	0.891	3.8
375	-	225	9.46e-12	-6	208.6	1.037e-8	0.868	405.8	1.179e-7	0.895	1.7
400	-	184		-	151	1.798e-8	0.825	185.6	8.823e-8	0.923	0.45
425		173.6		-	103.5	9.534e-8	0.899	70.7	1.973e-9	1	0.9

**Табл. S1.** Результаты моделирования импеданса образца согласно схеме на Рис. 5. **Table S1.** The results of modeling the impedance of the sample according to the scheme in Fig. 5.

**Табл. S2.** Результаты моделирования импеданса образца согласно схеме на Рис. 9.

 Table S2. The results of modeling the impedance of the sample according to the scheme in Fig. 9.

<i>Т</i> , °С	$R_1$ , W	C, pF	<i>R</i> <sub>2</sub> , W	T <sub>CPE1</sub>	P <sub>CPE1</sub>	<i>R</i> <sub>3</sub> , W	<i>R</i> <sub>4</sub> , W	T <sub>CPE2</sub>	P <sub>CPE2</sub>	$\chi^{2} \cdot 10^{4}$
100	2.395e5	14.2	72174	2.57e-9	0.914	6.8e6	457	1.007e-7	0.767	8.8
125	1.002e5	15.4	37388	2e-9	0.941	1.83e6	612	1.217e-7	0.777	9
150	45497	16.6	18945	2.07e-9	0.936	6.58e5	531	1.483e-7	0.777	3.4
175	22150	18.8	10005	2.44e-9	0.918	2.56e5	515	1.706e-7	0.788	2.1
200	11565	17.7	6151	3e-9	0.891	1.106e5	83	1.92e-7	0.794	2.4
225	6095	19.5	3713	2.22e-9	0.907	51249	92	2.26e-7	0.79	3
250	3494	18.7	2506	1.403e-9	0.947	23518	0	2.345e-7	0.8	4
275	2176	19.9	1771	1.585e-9	0.929	10644	0	2.27e-7	0.816	3.9
300	1374	22.4	1276	2.22e-9	0.896	4593	0	2.02e-7	0.837	3.7
325	909	8	768	2.78e-9	0.878	1968	0	1.577e-7	0.867	4.9
350	625.7	-	560	3.3e-9	0.858	877	0	1.27e-7	0.891	3.8
375	433.6	-	467.8	2.4e-9	0.868	405.8	0	1.18e-7	0.895	1.7
400*	335.3	-	406.7	3.74e-9	0.824	185	0	8.74e-8	0.924	0.4
425*	246	-	417.7	1.09e-8	0.931	101.4	0	2.11e-8	0.818	0.3



**Рис. S1.** (Color online) Температурные зависимости проводимостей  $\sigma_1$  (1) и  $\sigma_2$  (2) в аррениусовом масштабе, моделируемые резисторами  $R_1$  (1) и  $R_2$  (2).

**Fig. S1.** (Color online) Temperature dependences of conductivities  $\sigma_1(1)$  and  $\sigma_2(2)$  in Arrhenius scale, modeled by resistors  $R_1(1)$  and  $R_2(2)$ .



**Рис. 52.** Зависимость логарифма коэффициента корректировки диэлектрических потерь цепи «R2×CPE1» от температуры. **Fig. S2.** Dependence of the logarithm of the coefficient of correction of dielectric losses of the circuit "R2×CPE1" on temperature.